SiGe-THz devices: Physics and reliability



Chair: T. Zimmer (IMS Lab Univ. Bordeaux)

Download the slides @

http://www.iee.et.tu-dresden.de/iee/eb/res/dot7/dot7.html





Research in Europe on Bipolar Circuits and Technology

- RF2THz
 - Catrene
 - Cluster for Application and Technology Research in Europe on NanoElectronics
 - www.catrene.org/
- DOTSEVEN
 - 7th Framework Programme (European commission)
 - Integrated Project, section ICT: Information and Communication Technologies
 - http://cordis.europa.eu/fp7/ict/programme/



RF2THz at a glance

- The project CATRENE RF2THZ CT209 aims at the establishment of silicon technology platforms for emerging Radio Frequency (RF), Millimeter-Wave (MMW) and TeraHertz (THz) consumer applications.
- Duration:
 - 42 months: from 01.07.2011 to 31.12.2014
- Consortium:
 - 32 partners from 5 European countries
- Total effort:
 - 237.35PA
- Coordinator: Jean-Louis Carbonero (ST Microelectronics)



DOTSEVEN at a glance

- Development of a SiGe HBT technology with cut-off frequency (fmax) around 700 GHz (0.7 THz).
 - Demonstration of manufacturability and integratability with CMOS
 - Demonstration of capabilities and benefits of 0.7 THz SiGe HBT technology by benchmark circuits and system applications in the 0.1 to 1 THz range
- 6 European countries, 13 partners
- 42 months duration: from 01.10.2012 to 31.03.2016
- EC grant: 8.600.000€ for a budget of ~12M€
- Coordinator:
 - Rudolf Lachner INFINEON,
 - Deputy : Klaus Aufinger INFINEON
 - Technical Director: Michael Schroter, University Dresden, San Diego



Overview

- Open Bipolar Workshop dedicated to Research in Europe on bipolar circuits and technology
- 4 sessions
 - Session 1: Device physics(9h15-10h45)
 - Coffee Break: 10h45-11h00
 - Session 2: Safe-Operating-Area(11h00-12h30)
 - Lunch Break: 12h30-14h00
 - Session 3: Reliability (14h00-15h30)
 - Coffee Break: 15h30-15h45
 - Session 4: Design with Reliability (15h45-17h15)
 - 17h15-17h30 Q&A, 17h30 End of Workshop
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Or send a mail: thomas.zimmer@ieee.org



Programme

- Session 1: Physics based device simulation (9h15-10h45)
 - Christoph Jungemann, RWTH Aachen University
- Coffee Break: 10h45-11h00
- Session 2: Safe operating limits of SiGe-THz devices (11h00-12h30)
 - Anjan Chakravorty, IIT Madras, India, now guest professor at the University of Bordeaux
- Lunch Break: 12h30-14h00
- Session 3: Reliability of SiGe-THz devices (14h00-15h30)
 - Grazia Sasso, University of Naples, Italy now with Intel Germany
- Coffee Break: 15h30-15h45
- Session 4: Reliability aware circuit design (15h45-17h15)
 - Cristell Maneux, University of Bordeaux, France
- 17h30: End of SiGe-THz device Tutorial



Acknowledgement

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 - DOTSEVEN project supported by the European Commission through the Seventh Framework Programme for Research and Technological Development.
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